

TCE Type	Device Type	Applications	No. of Gates	Channel	Depl. or Enh. Mode	Maximum Ratings				
						Breakdown Voltages		Total Power Dissipatn.	Reverse Gate Current	Drain Current
						Gate-to-Source BV_{GS} V	Drain-to-Source BV_{DS} V			
SK3050	MOSFET	RF Amplifier, Mixer, IF Amplifier Stages	2	N	D	-6, +6 Peak	-0.2, +20	0.33		0.05
SK3065	MOSFET	RF Mixer and IF Stages	2	N	D	-6, +6 Peak	-0.2, +20	0.33	50 nA	0.050
SK3112	JFET	AF Small-Signal	1	N	D	-40	40	0.3	-10 nA	0.03
SK3448	JFET	Low-Noise Audio Preamplifier Stages	1	N	D			0.15	0.1 nA	$I_G = 10mA$
SK3746	JFET	General Purpose Amplifier	1	P	D	60 Min	$V_{DG} = 60V$	0.31	5 nA	$I_G = 10mA$
SK3834	JFET	VHF/UHF RF Amplifier	1	N	D	25 Min		0.31	1 nA	0.03
SK3977	JFET	General-Purpose Amplification, Switching	1	N	D	-30 Min		0.3	-0.1 nA	0.015
SK3991	MOSFET	VHF/UHF Amplifier, Mixer	2	N	D	30 Max	25 Min	0.36	-10 nA	0.03
SK4915	MOSFET	RF Amplifier for UHF TV Tuner	2	N	D		24	0.2	+/-20 nA	0.008 Max
SK9072	JFET	VHF/UHF Amplifier Applications	1	N	D	30 Min		0.3	100 pA	$I_G = 10mA$
SK9148	JFET	Low/Med. Freq. Differential Amplifiers	2	N	D	-50 Min		0.25	-100 pA	I_{G-50pA}
SK9149	JFET	Audio Amplifier/Chopper/Switch	1	N	D	-50 Min		0.3	-0.1 nA	0.01
SK9155	MOSFET	TTL and CMOS Interface	1	N	E		60 Min	1		0.5
SK9156	MOSFET	TTL and CMOS Interface	1	N	E		60 Min	0.315		0.25
SK9157	JFET	VHF Amplifiers	1	N	D	-30 Min		0.36	-1 nA Max	$I_G = -50mA$
SK9158	MOSFET	Low-Power Switching	1	N	E		25 Min	0.3		0.03
SK9160	MOSFET	Low-Power Audio-Frequency Circuits	1	N	D		25	0.3	1 pA Max	0.02
SK9161	JFET	General-Purpose Audio, Switching	1	N	D	-25 Min		0.31	-1 nA	$I_G = 10mA$
SK9162	JFET	High-Speed Switching, Chopper	1	N	D	30 Min		0.31	1 nA Max	
SK9163	JFET	Low-Power Switching, Chopper	1	N	D	-40 Min		0.36	0.25nA Max	
SK9164	JFET	VHF/UHF Amplifier	1	N	D	25 Min		0.31	1 nA Max	0.03
SK9165	MOSFET	Switching	1	N	E		180 Min	75		12
SK9460	JFET	Low-Noise Audio Amplifiers	1	N	D			0.3	-1 nA Max	$I_G = 10mA$
SK9500	MOSFET	Switching	1	N	E		150 Min	25		2
SK9501	MOSFET	Switching	1	N	E		150 Min	60		10
SK9502	MOSFET	Switching	1	N	E		500 Min	60		3
SK9503	MOSFET	Switching	1	N	E		60 Min	60		15
SK9504	MOSFET	Switching	1	P	E		-100 Min	8.33		1
SK9505	MOSFET	Switching	1	P	E		-150 Min	60		5
SK9506	MOSFET	Switching	1	P	E		-100 Min	60		6
SK9507	MOSFET	Switching	1	P	E		-100 Min	75		8
SK9508	MOSFET	Switching	1	P	E		-100 Min	75		12
SK9509	MOSFET	Switching	1	N	E		450 Min	75		6
SK9842	JFET	Low-Frequency/Low-Noise Amplifiers	1	P	E	20		0.3	10 nA	$I_G = 10mA$
SK9853	JFET	FM Tuners, VHF Amplifiers	1	N	E	$BV_{GDO} = 18V$ Min		0.2		$I_G = 10mA$
SK10126	MOSFET	Switching	1	N	E	500	500	75		2
SK10127	MOSFET	Med.-Voltage, High-Speed P-Ch. Enh.	1	P	E		500	75		2
SK10128	MOSFET	Med.-Voltage, High-Speed N-Ch. Enh.	1	N	E		100	75		8
SK10129	MOSFET	Power Field Effect Transistor	1	N	E	800	800	125		6
SK10130	MOSFET	High-Voltage, High-Speed N-Ch. Enh.	1	N	E		600	150		6
SK10131	MOSFET	N-Channel Enhancement Power	1	N	E		200	100		12
SK10132	MOSFET	Low-Voltage, High-Speed N-Ch. Enh.	1	N	E		60	75		12
SK10133	MOSFET	N-Channel Enhancement Mode Power	1	N	E		100 Min	150		38
SK10303	MOSFET	N-Channel Enhancement Mode	1	N	E	+20	500 Min	125		8
SK10304	MOSFET	N Channel Enhancement Mode	1	N	E		800	125		4
SK10462	JFET	N-Channel, Chopper/Switch	1	N	D	40	40	4		0.020
SK10463	JFET	N-Channel, Chopper/Switch	1	N	D		40	0.4		0.002
SK10465	JFET	P-Channel, General Purpose/Chopper	1	P	D	30		0.360		0.015



Operating Characteristics					Switching Characteristics, Max. Limits Resistive Load				Off-Time Delay	Outline No
Gate-to-Source Threshold-Voltage V_{GS} V	Forward Transcond. or Admittance g_{fs} μ mhos	Input Capacit. Short Circuit C_{iss} pF	Reverse Transfer Capacit. C_{rss} pF	Noise Figure NF	Drain-to-Source ON Resistance $r_{DS(ON)}$ Ohms	On-Time Delay $t_{d(ON)}$ nS	Rise Time t_r nS	Fall Time t_f nS		
-2	12000	6	0.02	3.5dB @ 200MHz	F-002	
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-1.5 Max	1200	20	37	4dB @ 120Hz	F-007	
1.5	3000	8	15	3dB @ 100Hz	F-005	
7.5 Max	5000 Max	5	1	1dB @ 100Hz	F-004	
6 Max	3500 Min	5 Max	1 Max	4dB @ 400MHz	F-006	
-6 Max	3500	4.5	1.2	2.5dB @ 100Hz	400	F-001	
-4 Max	22000 Max	0.03 Max	5dB @ 450MHz	F-002	
#	2.5	0.02	3.8dB @ 900MHz	S-044	
6 Max	7500 Max	4 Max	0.8 Max	2dB @ 100MHz	F-008	
-4.5 Max	6000 Max	6 Max	2 Max	3.5dB @ 10Hz	F-015	
-6	6500 Max	6 Max	3 Max	5dB @ 10Hz	F-008	
2.5 Max	200,000	48	2	5	5	F-009	
2.5 Max	200,000	48	2	5	5	F-010	
-6 Max	7500 Max	4.5 Max	1 Max	2dB @ 100MHz	F-011	
5 Max	1000 Min	5 Max	1.3 Max	300 Max	45	65	100	60	F-012
7 Max	2300	6	0.5	3.8dB @ 1kHz	F-013
-6 Max	3000	4.5	1.5	F-006
.....	10 Max	4 Max	30 Max	4	5	10	5	F-006
-10 Max	18 Max	8 Max	25 Max	6	3	25	F-014
4 Max	7000 Max	5 Max	1 Max	2dB @ 100MHz	F-006
4 Max	4 Min	1250	125	0.25 Max	35	130	105	120	F-016
.....	1500	13	3	5dB @ 10Hz	F-007
4 Max	400,000	150 Max	20 Max	2	17	30	17	30	F-016
4 Max	2 Min	650 Max	60 Max	0.3 Max	40	165	90	90	F-016
4 Max	1 mho	600 Max	50 Max	3 Max	30	40	50	90	F-016
4 Max	2 mhos Min	750 Max	180 Max	0.15	16	100	66	72	F-016
-2 Min	200,000	150 Max	30 Max	3.65 Max	7	15	11	14	F-017
-4 Max	0.75 mhos	700 Max	100 Max	1 Max	20	36	40	63	F-016
-4 Max	1 mho Min	800 Max	150 Max	0.6 Max	11	48	70	102	F-016
-4 Max	2 mhos Min	1500 Max	240 Max	0.4 Max	18	70	94	166	F-016
-4 Max	2 mhos Min	1500 Max	240 Max	0.3 Max	18	90	94	144	F-016
4 Max	2 mhos Min	1500 Max	100 Max	1.5 Max	15	40	60	190	F-016
.....	0.003 Max	T-101
-3	0.65 Max	1.8dB @ 100MHz	T-102
2-4.5	1 Min	500	50	T-126
4.5 Max	.5 mhos Min	100 Max	80 Max	6 Max	50 Max	100 Max	50 Max	150 Max	T-126
4.5 Max	1.5 mhos	400 Max	100 Max	0.5 Max	50 Max	120 Max	60 Max	50 Max	T-126
21-4	1.8 mhos Min	2000	80	T-127
4.5 Max	2 mhos Min	1800 Max	150 Max	1.2 Max	60 Max	150 Max	120 Max	200 Max	T-127
.....	4000. Min	1700 Max	300 Max	T-126
4.5 Max	3 mhos Min	800 Max	0.2 Max	60	160	110	80	T-126
4 Max	9-27 mhos	3000 Max	500 Max055 Max	35 Max	100 Max	100 Max	125 Max	T-127
2-4	7.4S umhos	1300	45	0.70	14	23	20	49	T-126
.....	3	T-126
.....	30	13	6	15	35	F-007
.....	6	3	100	13	8	15	35	F-007
2	6	20	4	F-007

G1 = -5.5V, G2 = -2.5V Max.

**UNIUNCTION TRANSISTORS (UJT)**

TCE Type	Maximum Ratings			Operating Characteristics				Outline No
	Total Power Dissipatn.	Emitter Current	Interbase Voltage	Intrinsic Standoff Ratio	Interbase Resistance	Peak-Point Emitter Current	Valley-Point Emitter Current	
	P_T mW	I_E mA	V_{B2B1} V	n^*	R_{BB} k Ω	I_P μ A	I_V μ A	
SK9121	300	50	35	0.70-0.85	4.0-9.1	1.0 Typ	7000 Typ	S-029
SK9122	450	50	35	0.47-0.80	4.0-12.0	25 Max	8000 Min	S-026
SK9123	300	50	35	0.56-0.75	4.7-9.1	1.0 Typ	6000 Typ	S-028
SK9124	300	50	35	0.68-0.82	4.7-9.1	1.0 Typ	10,000 Typ	S-028